

SmB₆: A material with anomalous energy distribution function of charge carriers?

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We argue that because of valence-fluctuation caused dynamical changes (fluctuations) of impurity energies in an impurity band of valence fluctuating semiconductors both occupied and unoccupied sites can be found in the impurity band above as well as below the Fermi level even in the ground state. As a consequence, the ground state energy distribution function of the subsystem of localized charge carriers for valence fluctuating semiconductors is qualitatively different than one for conventional semiconductors at $T = 0$ K, what sheds new light on interpretation of experimental results of valence fluctuating semiconductors, e.g. SmB₆ and YbB₁₂, at lowest temperatures.

SmB₆ is a prototypical mixed valence material revealing properties of a narrow-gap semiconductor down to few Kelvins [1–10]. Paradoxically, at lowest temperatures its conductivity exhibits presence of a temperature non-activated term [1–9], which however, cannot be attributed to any scattering scenario known for metals, because very high value of corresponding residual resistivity would require superunitary scattering [1–4]. According to Mott-Ioffe-Regel viewpoint, conventional Boltzmann transport theory becomes meaningless if the characteristic mean free path of the itinerant conduction electrons becomes comparable to, or less than the interatomic spacing [11, 12], so the requirement for superunitary scattering implicates that either (i) electrical conductivity is not homogeneous in the volume, i.e. material contains metallic regions forming along the sample a conductive path responsible for electrical conductivity at lowest temperatures [13–17] or (ii) electrical transport at lowest temperatures is realized via a hopping-type transport that in contrast to one in conventional semiconductors has to be temperature non-activated [18].

The first mentioned approach supposes metallic surface of SmB₆ which can be either of topological nature [13–16] or due to "trivial" polarity-driven surface states [17]. Indeed, many experimental observations indicate metallic surface transport in (stoichiometric) SmB₆ [19–21]. On the other hand, Raman scattering studies [22] showed that presence of even 1 % of Sm vacancies leads to smearing of the bulk hybridization gap in this material (being in qualitative agreement with earlier theoretical predictions [23]), and would result in a breakdown of the topological Kondo insulator state [22]. Other studies of vacant samples Sm_{1-x}B₆, for x ranging from 0.03 to 0.2, revealed resistivity saturation at lowest temperatures [24] similar to that of the stoichiometric SmB₆. Because concentration of Sm vacancies in these samples substantially exceeds level of 1 %, topologically protected surface states should not be present here, what implicates that scenario of topological Kondo insulator is not applicable in the case of all Sm-vacant samples.

The second above mentioned approach is represented

by the scenario of valence-fluctuation induced hopping transport [18] that is applicable also to vacant SmB₆-based samples. The key assumptions of this scenario, namely (i) presence of valence fluctuations (VFs), (ii) existence of an impurity band (IB), and (iii) the Fermi level lying in the IB, are in agreement with theoretical studies of impurity states in mixed-valent materials [23, 25, 26], studies of electrodynamic properties of SmB₆ in the low-frequency regime [6], optical conductivity studies of SmB₆ [27, 28], observation of presence of variable-range hopping transport in SmB₆ at lowest temperatures [7], and many other experimental observations reported for SmB₆ (see e.g. [6, 27–29] and references therein). As explained in [18], the energy of an impurity in the semiconductor with an IB that contains metallic ions in two different valency states (e.g. Me^{2+} and Me^{3+}) depends on the distribution of ion valences in the vicinity of this impurity (because of different interaction energy of this impurity with ions of different valency due to their different charge, ionic radii, and magnetic moment). Changes in distribution of ion valences unconditionally cause corresponding changes of the impurity energies and can be modeled by a rearrangement process (RP) with a characteristic time constant, t_r [18]. Thus, the energy E_i of the impurity i is not constant in time, but varies within some interval $\langle E_{i,min}, E_{i,max} \rangle$ [18]. Therefore, if the Fermi level, E_F , lies in the IB, there has to exist a subnetwork of impurities for which it is true that due to the RP some occupied impurity energy levels can shift from the region below E_F to the region above E_F , and analogously, some empty levels from the region above E_F can shift under E_F . This not only creates favorable conditions for temperature non-activated hops that are responsible for temperature non-activated transport [18], but also causes a *change* of energy distribution function (EDF) of charge carriers. It is the purpose of this work to point out that the EDF of localized charge carriers in the ground state of valence fluctuating semiconductors *qualitatively* differs from one expected for conventional semiconductors at $T = 0$ K, and that the absence of low temperature resistivity divergence in (real) SmB₆-based samples containing lattice imperfections can be a natural consequence of the changed EDF.

According to the "quantum-limit" hopping formula [30], the intrinsic transition rate γ_{ij} for an electron hop-

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ping from a site i with energy E_i to an empty site j with energy E_j in the simplest case, when $|E_j - E_i|$ is of the order of the Debye energy or smaller, and kT is small compared to $|E_j - E_i|$, can be expressed as

$$\gamma_{ij} = \gamma_0 e^{-2\alpha R_{ij} - (E_j - E_i)/kT} \text{ for } E_j > E_i \quad (1)$$

$$\gamma_{ij} = \gamma_0 e^{-2\alpha R_{ij}} \text{ for } E_j < E_i, \quad (2)$$

where k is Boltzmann constant, R_{ij} is the distance between sites i and j , and γ_0 is a constant, which depends on the electron-phonon coupling strength, the phonon density of states, and other properties of the material, but which depends only weakly on the energies E_i and E_j or on R_{ij} [30]. According to Eq. (2), the intrinsic transition rate of electron hop to a site of less energy decreases exponentially with increasing R_{ij} . However, because γ_0 is finite, γ_{ij} must be also finite, so there is always *non-zero* time interval t_h until an electron can hop (tunnel) to some empty site of less energy, while this time interval increases with increasing distance between the sites. If the RP (e.g. represented by VFs) is the ground state property of a material, finite γ_{ij} suggests a non-zero probability of finding some occupied energy levels above E_F also in the ground state. In a conventional semiconductor (i.e. one without the RP) the time averaged occupation number of site i in the thermal equilibrium (at neglecting electron-electron interactions except those causing that not more than one electron can occupy a single site) can be expressed in the form $\langle n_i \rangle = 1 / \{1 + \exp[(E_i - E_F)/kT]\}$ [30], what for $T = 0$ K unconditionally means that all energy levels below E_F are occupied and all energy levels above E_F are empty. Thus, the above mentioned non-zero probability to find occupied energy levels above E_F in the ground state implies that the ground-state EDF of the subsystem of localized charge carriers in materials with the RP is *qualitatively* different from the EDF in conventional semiconductors at $T = 0$ K. This fundamental conclusion we support by the following discussion.

According to the scenario of valence-fluctuation induced hopping transport [18], a hopping site i can be characterized by an energy interval of the typical width $E_0 \approx E_{i,max} - E_{i,min}$ and by the partial DOS, $g_i(E)$, which is non-zero and constant within the interval $\langle E_{i,min}, E_{i,max} \rangle$ and zero outside it (see Fig. 1a). Let us moreover characterize the site i by a time averaged probability of the occupation of this site by an electron, $p_i \in \langle 0, 1 \rangle$. Because time interval t_h until the electron can hop (tunnel) to an empty site of less energy increases with increasing distance between the sites, at very low concentration of impurities, or in case of the RP with a very short t_r (e.g. fast valence fluctuating process), it can be reasonably considered that $t_r \ll t_h$. This limit case practically means that electron occupies the state for sufficiently long time to receive any energy E_i from the interval $\langle E_{i,min}, E_{i,max} \rangle$. We define the time averaged probability of the occupation of site i by an electron, p_i , as the average value of the Fermi-Dirac distribution function (FDDF), $f_0(E_i, T) = 1 / \{1 + \exp[(E_i - E_F)/kT]\}$,

over the energy interval $\langle E_{i,min}, E_{i,max} \rangle$. Assuming that all energy intervals have the typical width E_0 (i.e. $E_0 \equiv E_{i,max} - E_{i,min}$), p_i can be expressed in the form

$$p_i(E_{i,c}, T, E_0) = \frac{1}{E_0} \int_{E_{i,c}-E_0/2}^{E_{i,c}+E_0/2} f_0(E_i, T) dE_i, \quad (3)$$

where $E_{i,c} = (E_{i,min} + E_{i,max})/2$. Fig. 1b shows p_i as defined by Eq. (3) calculated for $T = 0$ K and for fixed parameter E_0 . As can be seen, $p_i = 1$ for

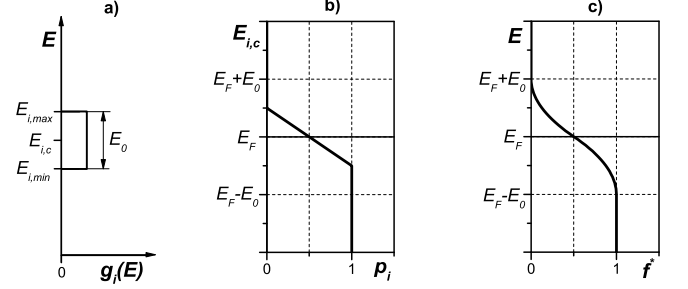


FIG. 1: Schematic depiction of the partial DOS, $g_i(E)$, of the impurity center in the IB as introduced in [18] (a), time averaged probability p_i of the occupation the site i having its energy interval centered at $E_{i,c}$ (b), and a time averaged probability of occupation of the state at energy E in the IB (c).

$E_{i,c} \leq E_F - E_0/2$, $p_i = 0$ for $E_{i,c} \geq E_F + E_0/2$, and p_i decreases linearly from 1 to 0 for $E_{i,c}$ in the interval $E_F - E_0/2 < E_{i,c} < E_F + E_0/2$. According to the above mentioned, all impurity sites having $E_{i,c}$ in the energy interval $E - E_0/2 < E < E + E_0/2$ are overlapped at energy E , and contribute to the probability of occupation of the state at energy E proportionally to $p_i(E_{i,c}, T, E_0)/E_0$. Thus we can determine the time averaged probability of occupation of the state at energy E in the IB (i.e. the EDF) as

$$f^*(E, T, E_0) = \int_{E-E_0/2}^{E+E_0/2} \frac{p_i(E_{i,c}, T, E_0)}{E_0} dE_{i,c}. \quad (4)$$

Analytical calculation of Eq. 4 for $T = 0$ K and for fixed E_0 gives

$$f^* = 1 \quad \text{for } E \leq E_F - E_0, \quad (5)$$

$$f^* = \frac{-E^2 - 2E_0E + E_0^2}{2E_0^2} \text{ for } E_F - E_0 \leq E \leq E_F, \quad (6)$$

$$f^* = \frac{E^2 - 2E_0E + E_0^2}{2E_0^2} \text{ for } E_F \leq E \leq E_F + E_0, \quad (7)$$

$$f^* = 0 \quad \text{for } E_F + E_0 \leq E, \quad (8)$$

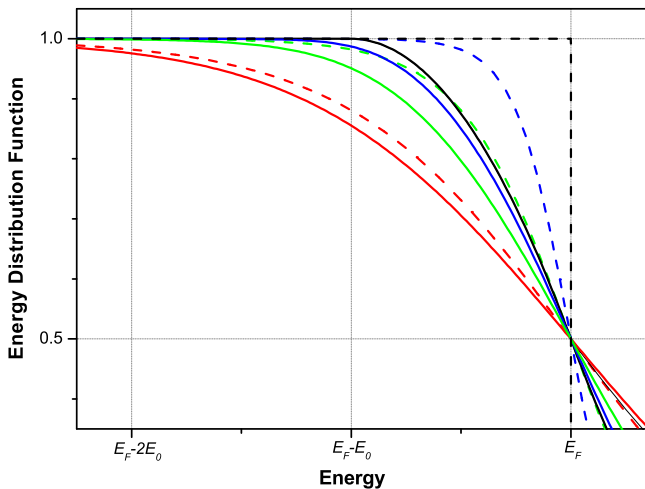


FIG. 2: Plots of f^* (solid lines) compared with FDDFs (dashed lines) for temperatures $T = 0$ K (black), $T = E_0/8k$ (blue), $T = E_0/4k$ (green) and $T = E_0/2k$ (red).

as depicted in Fig. 1c. As follows from Eqs. (5-8), the $f^*(E, 0 \text{ K}, E_0)$ is a continuous function with the finite slope $\partial f^*(E, 0 \text{ K}, E_0)/\partial E = -1/E_0$ at the Fermi level. This represents a qualitative difference in comparison with FDDF, since $\partial f_0(E, T)/\partial E = -1/4kT$ at E_F (giving infinite slope for $T = 0$ K). Considering that the slope of the EDF at E_F reflects energy broadening (either due to a non-zero temperature or due to the RP), both slopes can be compared yielding

$$E_0 \approx 4kT. \quad (9)$$

Fig. 2 shows numerically calculated plots of $f^*(E, T, E_0)$ for $T = 0$ K, $T = E_0/8k$, $T = E_0/4k$ and $T = E_0/2k$ compared with FDDFs calculated for the same temperatures. As can be seen, f^* for $T = 0$ K strongly differs from the FDDF at $T = 0$ K, and can be much better approximated by the FDDF at the finite temperature $T = E_0/4k$. As can be deduced from the plots for $T = E_0/8k$, the EDF of the system with the RP can be at sufficiently low temperatures much better approximated by the FDDF at $T = E_0/4k$ than by the FDDF at real temperature of the system. Thus it seems that the RP at lowest temperatures affects the EDF analogously as temperature enhanced to the value of $E_0/4k$. In general, all f^* curves have less (negative) slope at E_F in comparison with the slope of the FDDF (at E_F) at the same temperature, resembling the effect of a temperature enhancement due to the RP.

We suppose that the energy broadening as discussed above (for $t_r \ll t_h$) can be adopted also to the case of SmB_6 because of the fast valence fluctuation rates in this material [31]. Deducing from Eqs. (5-8) and Fig. 2, at sufficiently high temperatures (where E_0 is much less than thermal broadening) the EDF of localized charge carriers in SmB_6 will be practically unaffected by valence fluctuations (VFs). Approaching temperatures $T \approx$

$E_0/4k$ the EDF will exhibit essential deviation from the FDDF due to VFs, while at temperatures $T \ll E_0/4k$ the EDF will resemble the FDDF corresponding to significantly greater temperature, $T \approx E_0/4k$. Consequently, physical characteristics of SmB_6 that are governed by the EDF (e.g. electrical resistivity) will for $T \rightarrow 0$ K converge to those expected at a non-zero temperature, providing another reason for the absence of the resistivity divergence.

Here we would like to pay attention to some possible new phenomena which could take place at temperatures around and below $T \approx E_0/4k$. As follows from the definition (Eq. 4), $f^*(E, T, E_0)$ is the function of parameter E_0 , thus E_0 affects the energy of the subsystem of localized charge carriers. At the same time, E_0 reflects a "magnitude" of impurity energy fluctuation due to fluctuation of the properties of the surrounding lattice (because of VFs). Thus, E_0 can represent a "driving force" to minimize the total energy of the system. For instance, "tuning" of the processes associated with VFs (e.g. reasonable change of fluctuations in magnetic subsystem and the associated magnetic interactions/correlations) can yield such value of E_0 that the total energy will be minimized. Although at high temperatures ($T \gg E_0/4k$) E_0 will practically not affect the $f^*(E, T, E_0)$, the influence of E_0 can become essential approaching temperatures close to $T \approx E_0/4k$, and it may appear as favorable to change physical state of the system such way that the total energy will be minimized due to changed interactions and correspondingly changed value of E_0 . No clear conclusion can be done here whether eventual change of E_0 should be continuous in a certain temperature interval or "sudden", resembling a phase transition. Nevertheless it can be still expected that such change of E_0 will be associated with change of physical properties of the system in a certain temperature region. As possible (or perhaps accidental) analogy with the above provided picture we would like to mention very recent ESR studies of SmB_6 [29]. The ESR signal observed at $T = 5$ K was not more observed at $T = 6$ K [29]; moreover, the critical behavior of the integrated ESR intensity, $I(T) \sim (T^* - T)^\nu$, with characteristic temperature $T^* = 5.34 \pm 0.05$ K and exponent $\nu = 0.38 \pm 0.03$ was observed, and the authors [29] mentioned a possibility of "some abrupt structural/magnetic transition" to explain experimental results and emphasized the importance of re-considering "5 K anomaly" in context of modern topological physics of SmB_6 .

Finally, we would like to emphasize that presented results enable to explain absence of resistivity divergence at lowest temperatures in both stoichiometric, as well as in vacant SmB_6 samples. The scenario of valence-fluctuation induced hopping transport [18] and its consequences discussed here shed new light onto observations associated with "5 K anomaly" by inferring possible existence of new phenomena "driven" by the subsystem of localized charge carriers, while all these phenomena can be considered simultaneously with possible presence of

topologically protected or/and polarity-driven metallic surface states in SmB_6 . We believe that our findings not only represent a base for understanding the underlying physics in valence fluctuating semiconducting compounds at lowest temperatures, but that they also indicate a necessity to consider similar phenomena in many other materials with "dynamical ground state", especially those

obeying physical properties which cannot be adequately understood presumably supposing the ground state being associated with the FDDF for absolute zero.

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